

## **Erratum: The Fermi level is not pinned at the $p$ -GaAs(100) surface during adsorption of cesium and oxygen [JETP Lett. 55, 288–292 (1992)]**

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On page 291, the last sentence of the second paragraph should read: “The apparent reason for the fundamental differences between the results found here and the results found on cleaved (110) faces<sup>1</sup> appears to lie in the special properties of the (100) surface.<sup>11</sup>”